

SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURE OF THE SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE

The semiconductor laser device has a lower clad layer, an active layer, an upper clad layer, a forward mesa forming layer, a contact layer and an insulating film, sequentially formed on the semiconductor substrate.

5 The upper clad layer, the forward mesa forming layer, the contact layer and the insulating film form a ridge. The etching speed of the forward mesa forming layer is higher than that of the upper clad layer and lower than that of the contact layer. Because of such etching speeds, the

10 ridge having a forward mesa structure is formed.

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